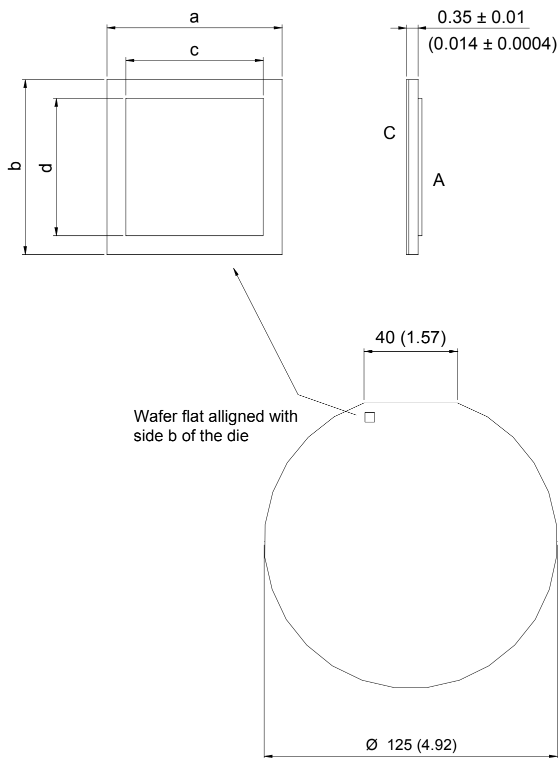
International
IOR Rectifier

# FD200H02A5B

## Fred Die in Wafer Form




NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

2. CONTROLLING DIMENSION (INCH):

3. DIMENSIONS AND TOLERANCES:
   **a = 5.080 ± 0.05**
   **(0.200 ± 0.002)**
   **b = 5.08 ± 0.05**
   **(0.200 ± 0.002)**
   **c = 4.420 ± 0.003**
   **(0.174 ± 0.0001)**
   **d = 4.420 ± 0.003**
   **(0.174 ± 0.0001)**

4. LETTER DESIGNATION:
   A = Anode (Top Metal)
   C = Cathode (Back Metal)

5. SAWING:
   Recommended Blade
   SEMITEC S1025 QS00 Blade

6. MINIMUM ORDER QUANTITY:
   **300** die

NOT TO SCALE

## Electrical Characteristics (Wafer Form)

| | Parameters | Units | Test Conditions |
|---|---|---|---|
| $V_{FM}$ | Maximum Forward Voltage | 1.13 V | $T_J$ = 25°C, $I_F$ = 150 A (Pow*IR*tab) |
| $V_{FM}$ | Maximum Forward Voltage | 1.08 V | $T_J$ = 25°C, $I_F$ = 60 A (TO-247) |
| $V_{RRM}$ | Mimunum Reverse Breakdown Voltage | 200 V | $T_J$ = 25°C, $I_{RRM}$ = 100 µA |
| $I_{RM}$ | Max. Reverse Leakage Current | 50 µA | $T_J$ = 25°C, $V_{RRM}$ = 200 V |
| $t_{rr}$ | Typ. Reverse Recovery Time | 35 ns | $I_F$ = 1A, di/dt = 100A/µs, $V_R$ = 30 V |

## Mechanical Data

| | |
|---|---|
| Nominal Back Metal Composition, Thickness | Cr - Ni - Ag (1 KA - 2 KA - 3 KA) |
| Nominal Front Metal Composition, Thickness | 99% Al, 1% Si (3 microns) |
| Chip Dimensions | 0.200" x 0.200" (see drawing) |
| Reject Ink Dot Size | 0.25 mm diameter minimum |
| Recommended Storage Environment | Storage in original container, in dessicated nitrogen, with no contamination |

## Ordering Information Table

**Device Code**

| FD | 200 | H | 02 | A | 5 | B |
|---|---|---|---|---|---|---|
| 1 | 2 | 3 | 4 | 5 | 6 | 7 |

1 - Fred Die
2 - Chip Dimension in Mils: 200 = 200x200 square
3 - Process H = HyperFast
4 - Voltage code Vrrm (*100) eg: 02 = 200V
5 - Chip surface metallization: A = Aluminium (anode), Silver (cathode)
6 - Wafer diameter in inches
7 - Packaging: B = Inked Probed Unsawn Wafer (Wafer in box)